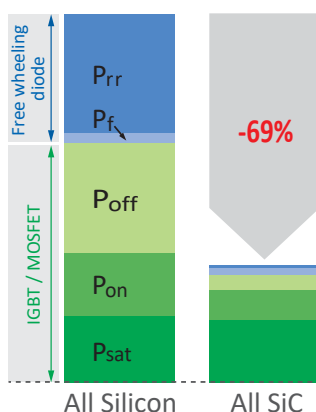


All SiC 2 in 1 Modules

SiC MOSFET & SiC Schottky diode

Power dissipation at 16 kHz
AllSiC vs. All Silicon
Module rating: 1200V / 35 A

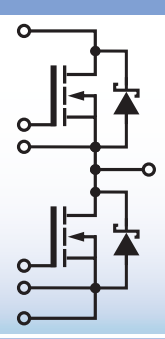
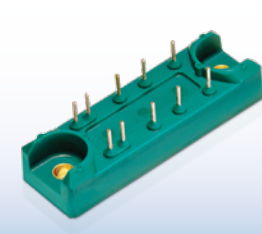




Optimum performance:

Combining the AllSiC technology with the new package concept

- **Thick copper block with isolation substrate**
 - Low thermal impedance & effective heat spreading
- **Interconnection by copper pins instead of wire bonding**
 - Downsizing, Low inductance, Very high reliability
- **High temperature epoxy resin, no silicone gel**
 - High temperature strength ($T_g > 200^\circ\text{C}$)

Line-up plan of Fuji Electric Green Package, 2 in 1

	Type 1	Type 2	Type 3L
 <p>1200V 1st gen. TrenchMOS</p>	 <p>25 A, 50 A</p>	 <p>75 A, 100 A</p>	 <p>200 A, 300 A, 400 A</p>